

150V N-Channel Enhancement Mode MOSFET

Description

The XPX40N15FD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 150V$ $I_D = 40A$

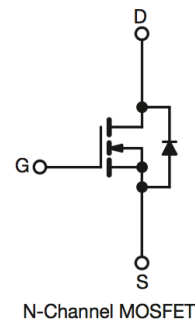
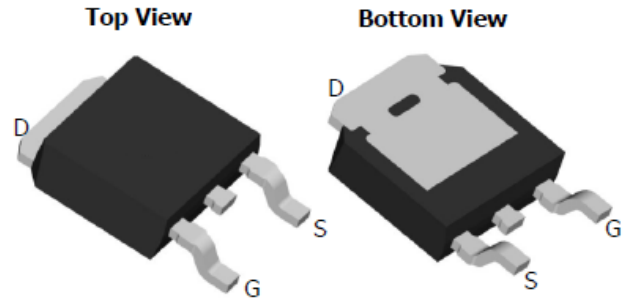
$R_{DS(ON)} < 46m\Omega$ @ $V_{GS}=10V$

Application

DC/DC Converter

LED Backlighting

Power Management Switches



Package Marking and Ordering Information

| Product ID | Pack | Marking | Qty(PCS) |
|------------|-----------|---------------------|----------|
| XPX40N15FD | TO-252-3L | XPX40N15FD XXX YYYY | 2500 |

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Rating | Units |
|-----------------------------|--|------------|---------------------------|
| V_{DS} | Drain-Source Voltage | 150 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_C=25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10V$ | 40 | A |
| $I_D@T_C=100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10V$ | 28 | A |
| IDM | Pulsed Drain Current | 120 | A |
| EAS | Single Pulse Avalanche Energy | 216 | mJ |
| IAS | Avalanche Current | 38 | A |
| $P_D@T_C=25^\circ\text{C}$ | Total Power Dissipation ⁴ | 115 | W |
| TSTG | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient | 1.3 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case | 62.5 | $^\circ\text{C}/\text{W}$ |

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Electrical Characteristics (T_C=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|--|------|------|------|------|
| BVDSS | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 150 | --- | --- | V |
| RDS(ON) | Static Drain-Source On-Resistance ² | V _{GS} =10V, I _D =20A | --- | 46 | 46 | mΩ |
| | Static Drain-Source On-Resistance ² | V _{GS} =4.5V, I _D =20A | --- | 37 | 50 | mΩ |
| VGS(th) | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =250uA | 1.2 | 2.0 | 2.5 | V |
| IDSS | Drain-Source Leakage Current | V _{DS} =120V, V _{GS} =0V, T _J =25°C | --- | --- | 1 | uA |
| | | V _{DS} =120V, V _{GS} =0V, T _J =55°C | --- | --- | 5 | |
| IGSS | Gate-Source Leakage Current | V _{GS} =±20V, V _{DS} =0V | --- | --- | ±100 | nA |
| gfs | Forward Transconductance | V _{DS} =5V, I _D =20A | --- | 55 | --- | S |
| Qg | Total Gate Charge (4.5V) | V _{DS} =75V, V _{GS} =4.5V, I _D =10A | --- | 40 | --- | nC |
| Qgs | Gate-Source Charge | | --- | 10 | --- | |
| Qgd | Gate-Drain Charge | | --- | 21 | --- | |
| Td(on) | Turn-On Delay Time | V _{DD} =50V, V _{GS} =4.5V, R _G =3.3Ω, I _D =10A | --- | 18 | --- | ns |
| T _r | Rise Time | | --- | 20 | --- | |
| Td(off) | Turn-Off Delay Time | | --- | 65 | --- | |
| T _f | Fall Time | | --- | 15 | --- | |
| Ciss | Input Capacitance | V _{DS} =25V, V _{GS} =0V, f=1MHz | --- | 3753 | --- | pF |
| Coss | Output Capacitance | | --- | 206 | --- | |
| Crss | Reverse Transfer Capacitance | | --- | 160 | --- | |
| IS | Continuous Source Current ^{1,5} | V _G =V _D =0V, Force Current | --- | --- | 30 | A |
| VSD | Diode Forward Voltage ² | V _{GS} =0V, I _S =1A, T _J =25°C | --- | --- | 1.2 | V |
| trr | Reverse Recovery Time | I _F =10A, dI/dt=100A/μs, T _J =25°C | --- | 35 | --- | nS |
| Q _{rr} | Reverse Recovery Charge | | --- | 120 | --- | nC |

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=38A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

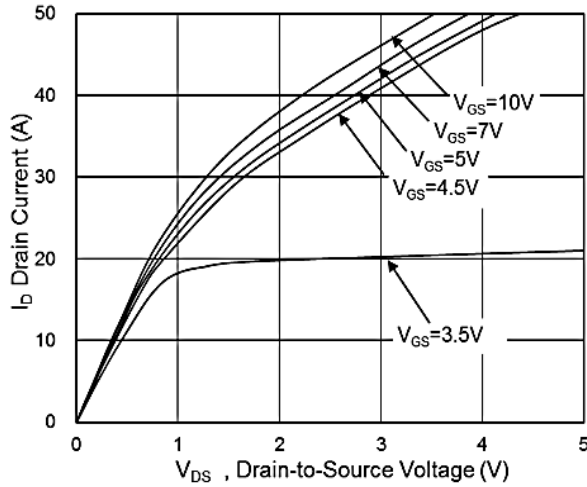


Fig.1 Typical Output Characteristics

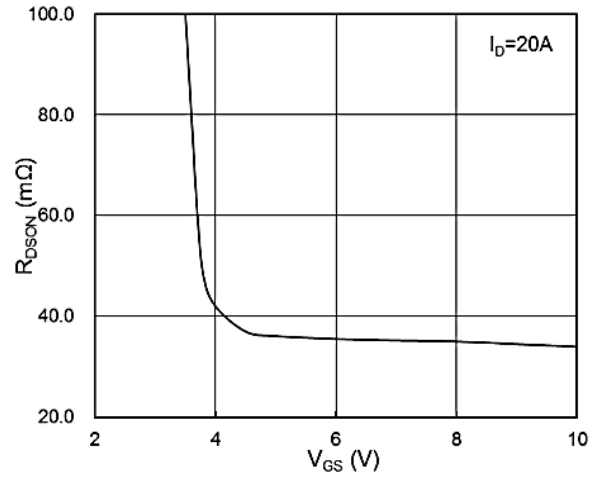


Fig.2 On-Resistance vs. Gate-Source

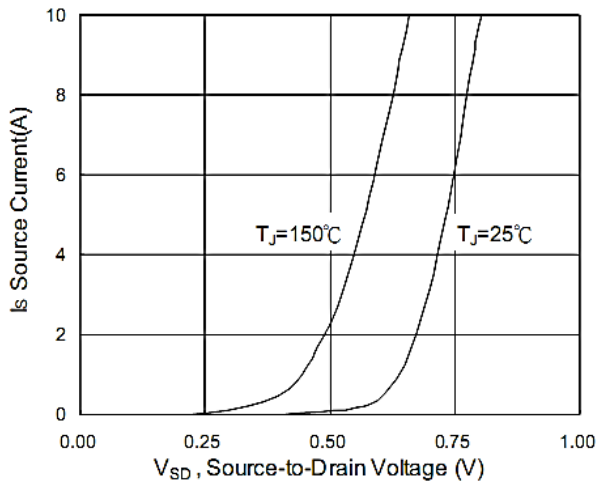


Fig.3 Forward Characteristics Of Reverse

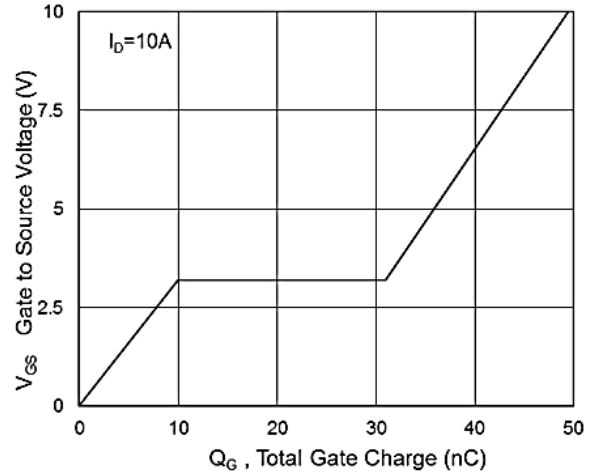


Fig.4 Gate-Charge Characteristics

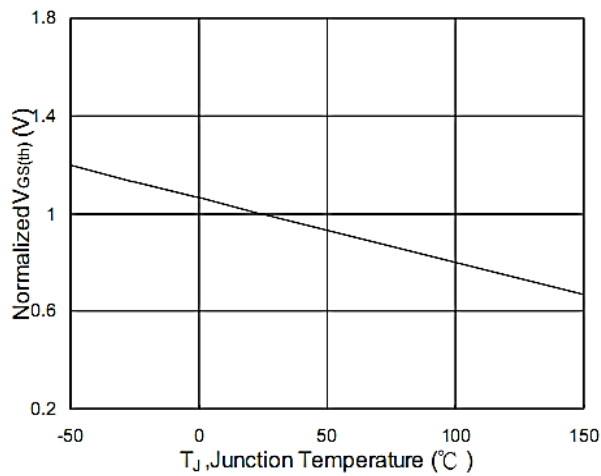


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

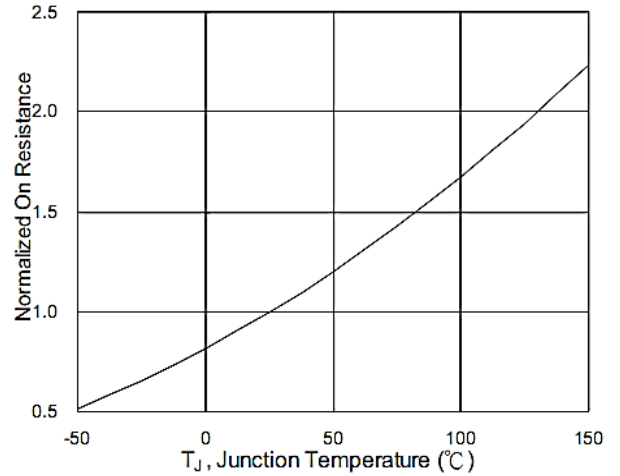


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

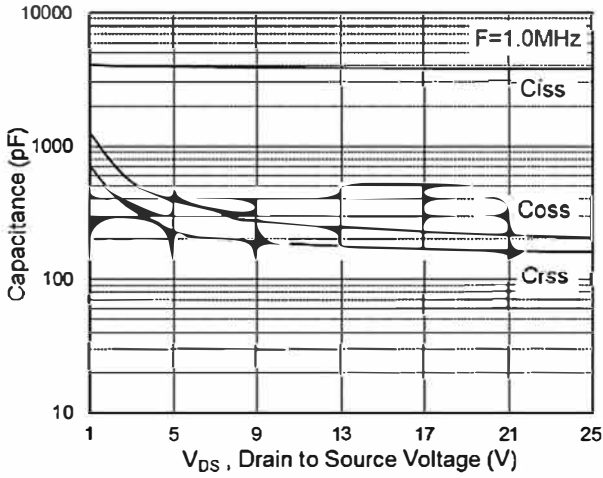


Fig.7 Capacitance

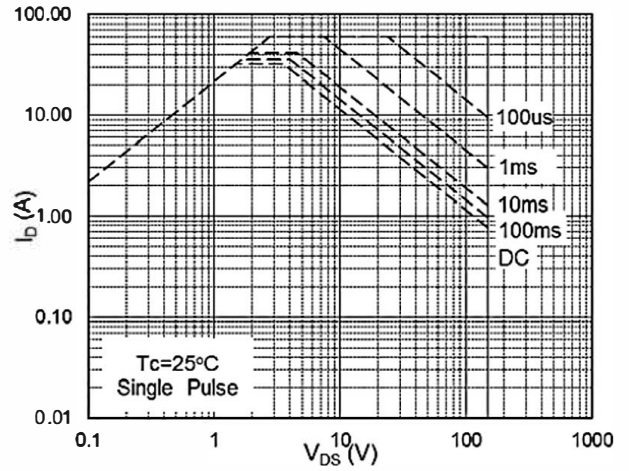


Fig.8 Safe Operating Area

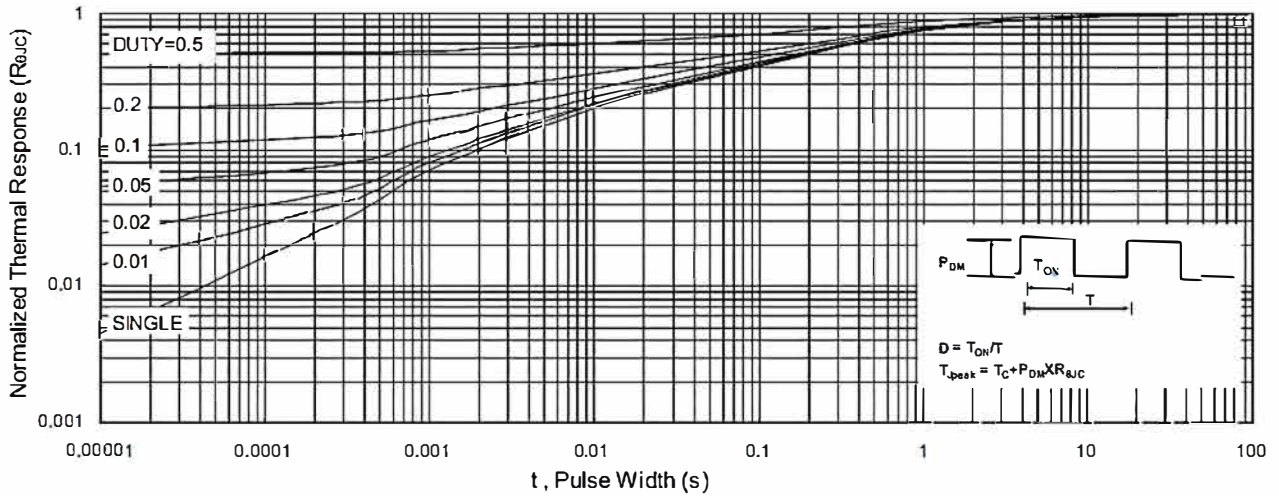


Fig.9 Normalized Maximum Transient Thermal Impedance

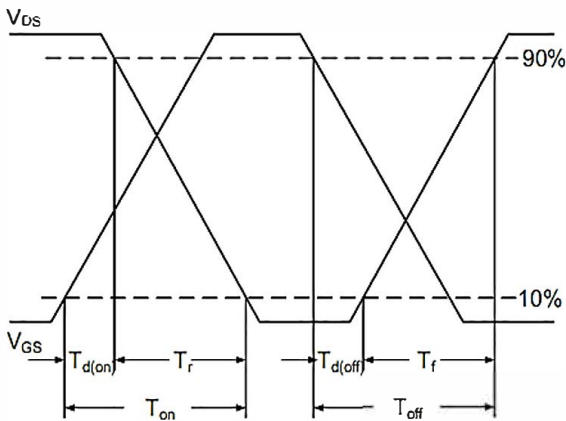


Fig.10 Switching Time Waveform

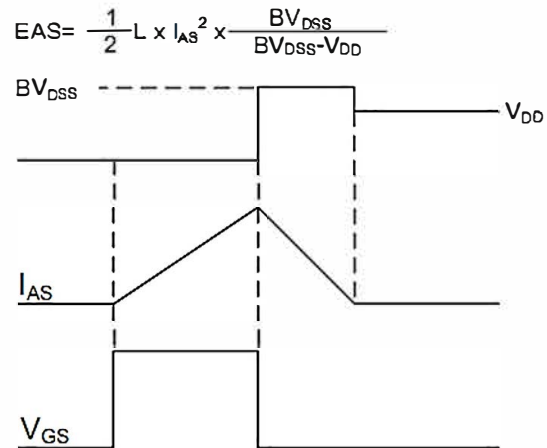
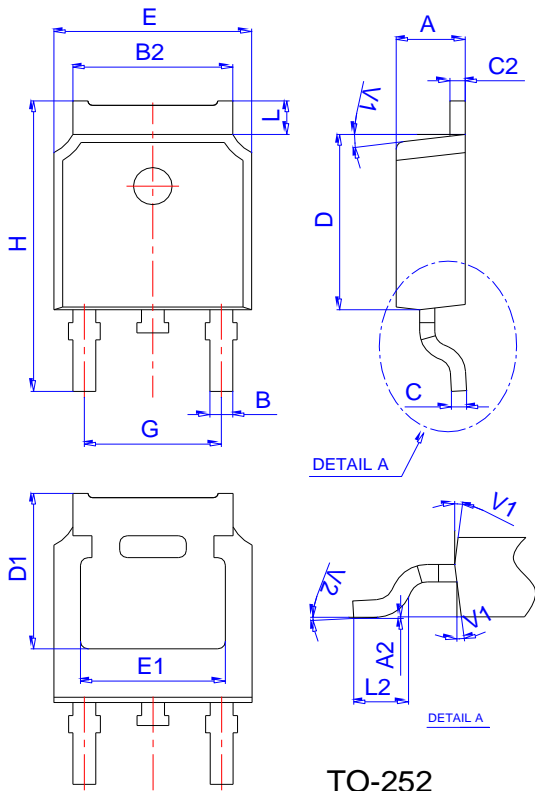


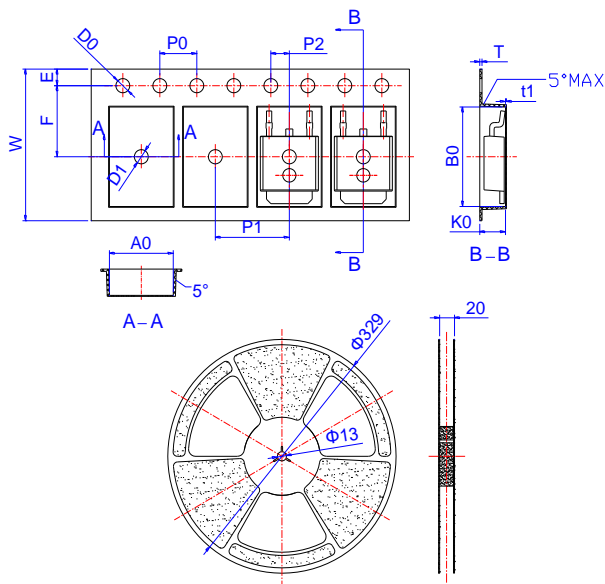
Fig.11 Unclamped Inductive Switching Waveform

150V N-Channel Enhancement Mode MOSFET



| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|----------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.10 | | 2.50 | 0.083 | | 0.098 |
| A2 | 0 | | 0.10 | 0 | | 0.004 |
| B | 0.66 | | 0.86 | 0.026 | | 0.034 |
| B2 | 5.18 | | 5.48 | 0.202 | | 0.216 |
| C | 0.40 | | 0.60 | 0.016 | | 0.024 |
| C2 | 0.44 | | 0.58 | 0.017 | | 0.023 |
| D | 5.90 | | 6.30 | 0.232 | | 0.248 |
| D1 | 5.30REF | | | 0.209REF | | |
| E | 6.40 | | 6.80 | 0.252 | | 0.268 |
| E1 | 4.63 | | | 0.182 | | |
| G | 4.47 | | 4.67 | 0.176 | | 0.184 |
| H | 9.50 | | 10.70 | 0.374 | | 0.421 |
| L | 1.09 | | 1.21 | 0.043 | | 0.048 |
| L2 | 1.35 | | 1.65 | 0.053 | | 0.065 |
| V1 | | 7° | | | 7° | |
| V2 | 0° | | 6° | 0° | | 6° |

Reel Specification-TO-252



| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| W | 15.90 | 16.00 | 16.10 | 0.626 | 0.630 | 0.634 |
| E | 1.65 | 1.75 | 1.85 | 0.065 | 0.069 | 0.073 |
| F | 7.40 | 7.50 | 7.60 | 0.291 | 0.295 | 0.299 |
| D0 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| D1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| P0 | 3.90 | 4.00 | 4.10 | 0.154 | 0.157 | 0.161 |
| P1 | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| P2 | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| A0 | 6.85 | 6.90 | 7.00 | 0.270 | 0.271 | 0.276 |
| B0 | 10.45 | 10.50 | 10.60 | 0.411 | 0.413 | 0.417 |
| K0 | 2.68 | 2.78 | 2.88 | 0.105 | 0.109 | 0.113 |
| T | 0.24 | | 0.27 | 0.009 | | 0.011 |
| t1 | 0.10 | | | 0.004 | | |
| 10P0 | 39.80 | 40.00 | 40.20 | 1.567 | 1.575 | 1.583 |

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Flow (wave) soldering (solder dipping)

| Product | Peak Temperature | Dipping Time |
|----------------|------------------|--------------|
| Pb device | 245°C ±5°C | 5sec±1sec |
| Pb-Free device | 260°C +0/-5°C | 5sec±1sec |



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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